

Field Effect Transistor Silicon P Channel MOS Type

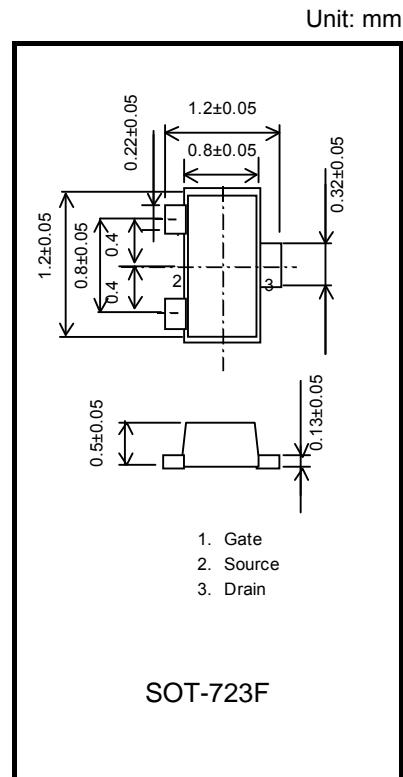
High Speed Switching Applications

Analog Switch Applications

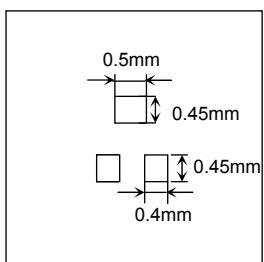
- Small package
- Low on-resistance : $R_{on} = 8 \Omega$ (max) (@ $V_{GS} = -4$ V)
- : $R_{on} = 12 \Omega$ (max) (@ $V_{GS} = -2.5$ V)
- : $R_{on} = 45 \Omega$ (max) (@ $V_{GS} = -1.5$ V)

Absolute Maximum Ratings (Ta = 25°C)

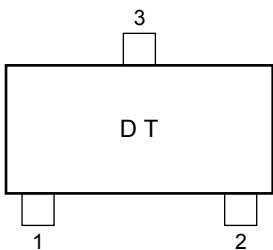
Characteristics	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	-20	V
Gate-Source voltage	V_{GSS}	± 10	V
Drain current	DC I_D	-100	mA
	Pulse I_{DP}	-200	
Drain power dissipation (Ta = 25°C)	P_D (Note 1)	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature range	T_{stg}	-55~150	°C



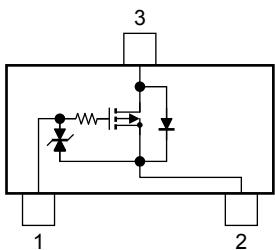
Weight :1.5mg



Marking



Equivalent Circuit (top view)

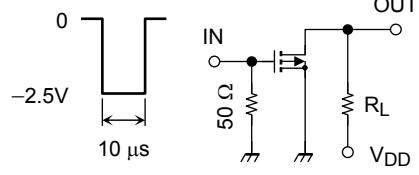


Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	MIN.	TYP.	MAX.	UNIT	
Gate leakage current	I_{GSS}	$V_{GS} = \pm 10\text{ V}, V_{DS} = 0$	—	—	± 1	μA	
Drain-Source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$I_D = -0.1\text{ mA}, V_{GS} = 0$	-20	—	—	V	
Drain cut-off current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0$	—	—	-1	μA	
Gate threshold voltage	V_{th}	$V_{DS} = -3\text{ V}, I_D = -0.1\text{ mA}$	-0.6	—	-1.1	V	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -3\text{ V}, I_D = -10\text{ mA}$	25	—	—	mS	
Drain-Source on-resistance	$R_{DS(\text{ON})}$	$I_D = -10\text{ mA}, V_{GS} = -4\text{ V}$	—	6	8	Ω	
		$I_D = -10\text{ mA}, V_{GS} = -2.5\text{ V}$	—	8	12		
		$I_D = -1\text{ mA}, V_{GS} = -1.5\text{ V}$	—	18	45		
Input capacitance	C_{iss}	$V_{DS} = -3\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	11	—	pF	
Reverse transfer capacitance	C_{rss}		—	3.7	—	pF	
Output capacitance	C_{oss}		—	10	—	pF	
Switching time	Turn-on time	t_{on}	$V_{DD} = -3\text{ V}, I_D = -10\text{ mA}, V_{GS} = 0 \sim -2.5\text{ V}$	—	130	—	ns
	Turn-off time	t_{off}		—	190	—	

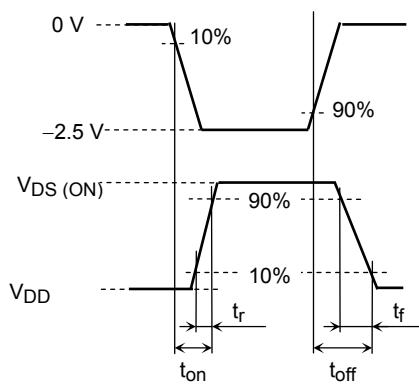
Switching Time Test Circuit

(a) Test circuit



$V_{DD} = -3\text{ V}$
 Duty $\leq 1\%$
 V_{IN} : $t_r, t_f < 5\text{ ns}$
 $(Z_{out} = 50\Omega)$
 Common Source
 $T_a = 25^\circ\text{C}$

(b) V_{IN}



(c) V_{OUT}

